

NPN Silicon Transistor KSC5026M

Features

- High Voltage and High Reliability
- High Speed Switching
- Wide SOA

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	1100	V	
V _{CEO}	Collector-Emitter Voltage	800	V	
V _{EBO}	Emitter-Base Voltage	7	V	
I _C	Collector Current (DC)	1.5	Α	
I _{CP}	Collector Current (Pulse)	5	Α	
Ι _Β	Base Current	0.8	Α	
Pc	Collector Dissipation (T _C = 25°C)	20	W	
TJ	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 to 150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



TO-126-3LD CASE 340AS

MARKING DIAGRAM



&3 = Date Code (Year & Week) C5026M = Specific Device Code O = h_{FE} Grade

ORDERING INFORMATION

Device	Package	Shipping	
KSC5026MOS	TO-126-3 (Pb-Free)	2000 Units / Bulk Bag	

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KSC5026N

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Test Condition	Min	Тур.	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 1 mA, I _E = 0	1100	-	_	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 5 mA, I _B = 0	800	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1 mA, I _C = 0	7	-	-	V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 0.75 \text{ A},$ $I_{B1} = -I_{B2} = 0.15 \text{ A},$ L = 5 mH, Clamped	800	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} = 800 V, I _E = 0	_	-	10	μΑ
I _{EBO}	Emitter Cut-off Current	V _{EB} = 5 V, I _C = 0	-	-	10	μΑ
h _{FE1} h _{FE2}	DC Current Gain	V _{CE} = 5 V, I _C = 0.1 A V _{CE} = 5 V, I _C = 0.5 A	10 8	- -	40 -	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 0.75 A, I _B = 0.15 A	-	-	2	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 0.75 A, I _B = 0.15 A	-	-	1.5	V
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	-	35	_	pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 0.1 A	-	15	-	MHz
t _{ON}	Turn On Time	V _{CC} = 400 V	_	_	0.5	μs
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 1 \text{ A}$ $R_L = 400 \Omega$	-	_	3	μs
t _F	Fall Time		_	_	0.3	μS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$h_{\mbox{\scriptsize FE}}$ CLASSIFICATION

Classification	N	R	0
h _{FE1}	10 ~ 20	15 ~ 30	20 ~ 40

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TYPICAL CHARACTERISTICS

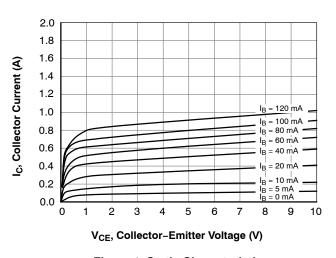


Figure 1. Static Characteristic

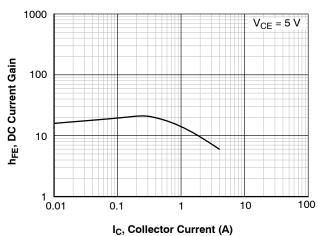


Figure 2. DC Current Gain

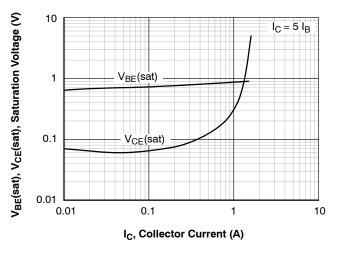


Figure 3. Base–Emitter Saturation Voltage Collector–Emitter Saturation Voltage

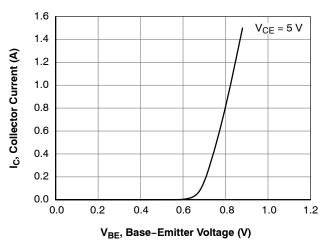


Figure 4. Base-Emitter On Voltage

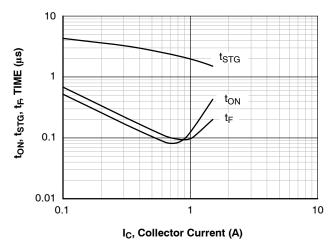


Figure 5. Switching Time

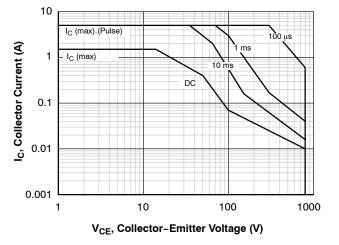
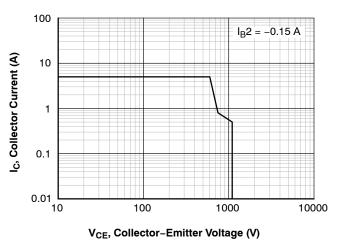


Figure 6. Safe Operating Area

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TYPICAL CHARACTERISTICS (Continued)





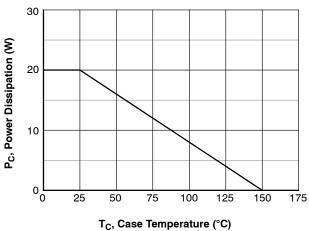
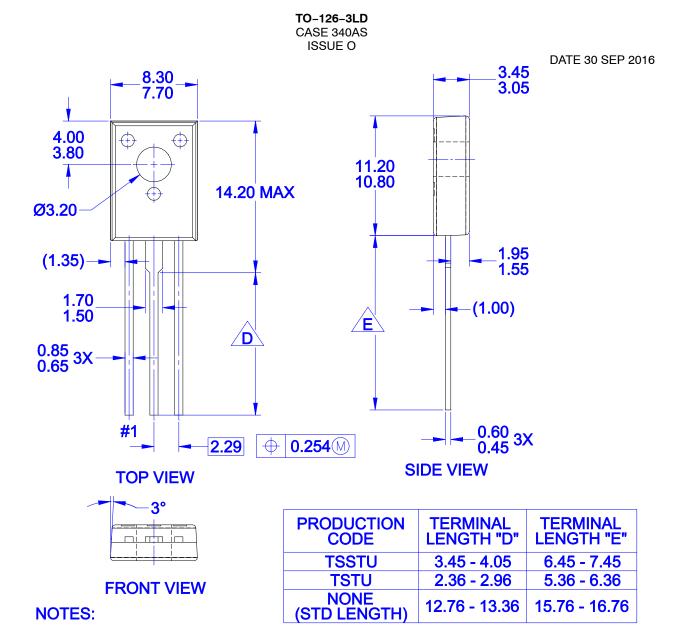


Figure 8. Power Derating





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- B. ALL DIMENSIONS ARE IN MILLIMETERS
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS



E FOR TERMINAL LENGTH "E", REFER TO TABLE

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